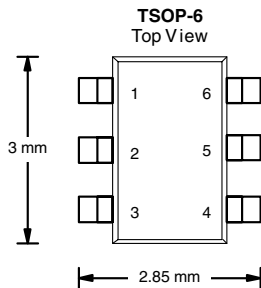
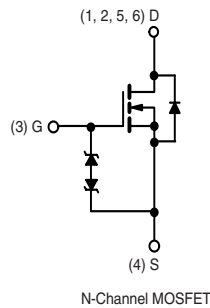


Automotive N-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	40
$R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V	0.032
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5$ V	0.046
I_D (A)	4.0
Configuration	Single



Marking Code: 8Hxxx


FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- Compliant to RoHS Directive 2002/95/EC
- AEC-Q101 Qualified^d
- Typical ESD Protection 800 V
- Find out more about Vishay's Automotive Grade Product Requirements at: www.vishay.com/applications


RoHS
COMPLIANT
HALOGEN
FREE

ORDERING INFORMATION	
Package	TSOP-6
Lead (Pb)-free and Halogen-free	SQ3418EEV-T1-GE3

ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 12	
Continuous Drain Current ^a	I_D	$T_C = 25$ °C	7.4
		$T_C = 125$ °C	4.0
Continuous Source Current (Diode Conduction) ^a	I_S	2.9	A
Pulsed Drain Current ^b	I_{DM}	20	
Single Pulse Avalanche Current	I_{AS}	10	
Single Pulse Avalanche Energy	E_{AS}	7	mJ
Maximum Power Dissipation ^b	P_D	$T_C = 25$ °C	2.0
		$T_A = 25$ °C	1.3
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	R_{thJA}	62.5	°C/W
Junction-to-Foot (Drain)	R_{thJF}	35	

Notes

- Package limited.
- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR-4 material).
- Parametric verification ongoing.

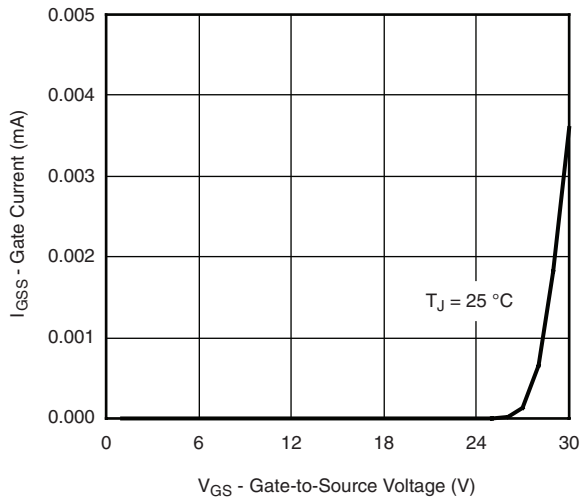
SPECIFICATIONS $T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = -250\text{ }\mu\text{A}$	40	-	-	V	
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250\text{ }\mu\text{A}$	1.5	-	2.5		
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 12\text{ V}$	-	-	± 100	nA	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}$	$V_{DS} = 40\text{ V}$	-	-	1	μA
		$V_{GS} = 0\text{ V}$	$V_{DS} = 40\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$	-	-	50	
		$V_{GS} = 0\text{ V}$	$V_{DS} = 40\text{ V}$, $T_J = 175\text{ }^\circ\text{C}$	-	-	150	
On-State Drain Current ^a	$I_{D(on)}$	$V_{GS} = 10\text{ V}$	$V_{DS} \geq 5\text{ V}$	10	-	-	A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 5\text{ A}$	-	0.029	0.032	Ω
		$V_{GS} = 4.5\text{ V}$	$I_D = 4\text{ A}$	-	0.038	0.046	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}$, $I_D = 4\text{ A}$		-	22	-	S
Dynamic^b							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$	$V_{DS} = 20\text{ V}$, $f = 1\text{ MHz}$	-	640	-	μF
Output Capacitance	C_{oss}			-	73	-	
Reverse Transfer Capacitance	C_{rss}			-	41	-	
Total Gate Charge ^c	Q_g	$V_{GS} = 4.5\text{ V}$	$V_{DS} = 20\text{ V}$, $I_D = 4\text{ A}$	-	12	-	nC
Gate-Source Charge ^c	Q_{gs}			-	1.9	-	
Gate-Drain Charge ^c	Q_{gd}			-	1.7	-	
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = 20\text{ V}$, $R_L = 4\text{ }\Omega$ $I_D \cong 5\text{ A}$, $V_{GEN} = 4.5\text{ V}$, $R_g = 1\text{ }\Omega$		-	16	-	ns
Rise Time ^c	t_r			-	17	-	
Turn-Off Delay Time ^c	$t_{d(off)}$			-	16	-	
Fall Time ^c	t_f			-	10	-	
Source-Drain Diode Ratings and Characteristics $T_C = 25\text{ }^\circ\text{C}$ ^b							
Pulsed Current ^a	I_{SM}			-	-	20	A
Forward Voltage	V_{SD}	$I_F = 1.7\text{ A}$, $V_{GS} = 0\text{ V}$		-	0.78	1.2	V

Notes

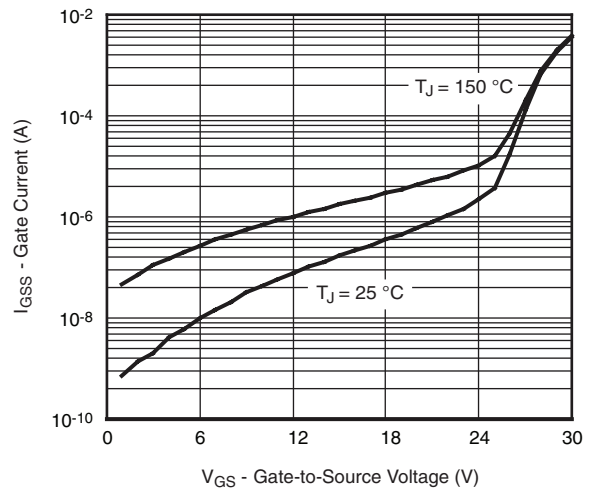
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

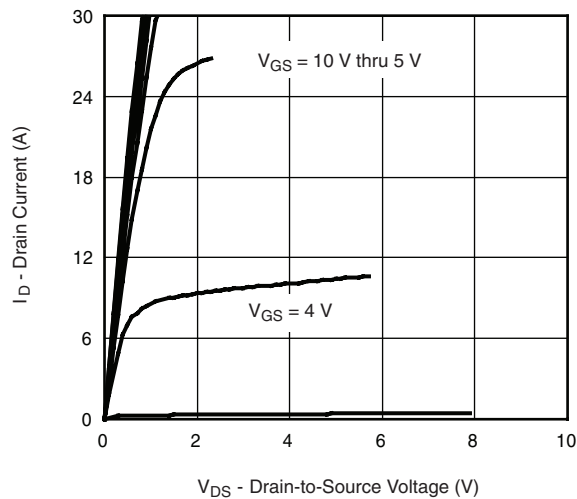
TYPICAL CHARACTERISTICS $T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted



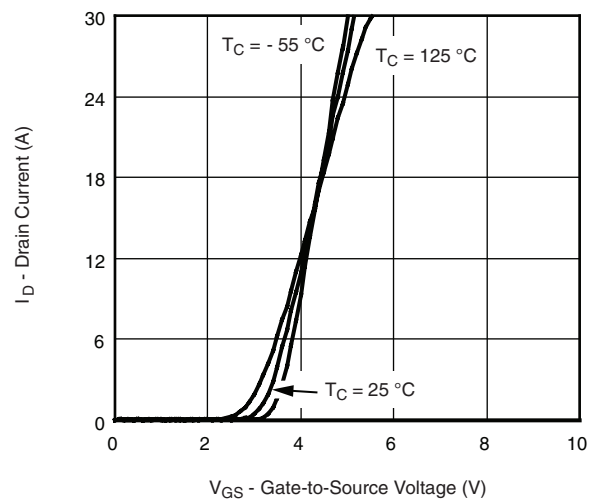
Gate Current vs. Gate-Source Voltage



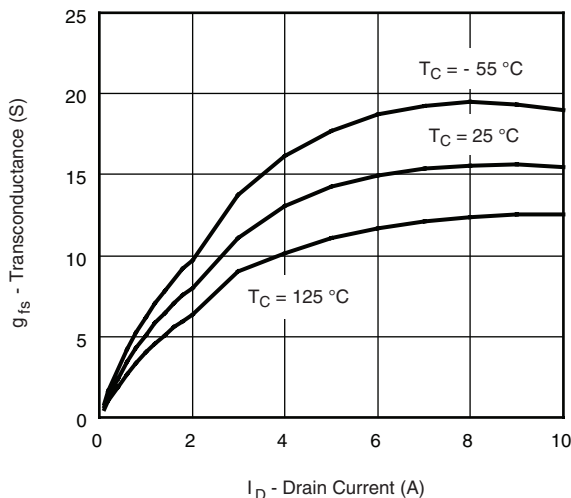
Gate Current vs. Gate-Source Voltage



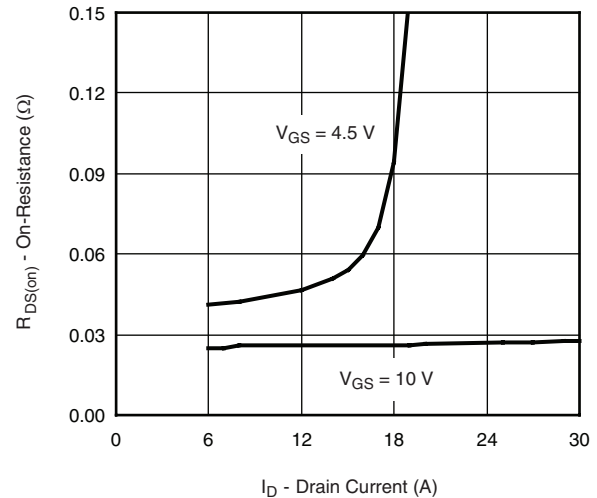
Output Characteristics



Transfer Characteristics

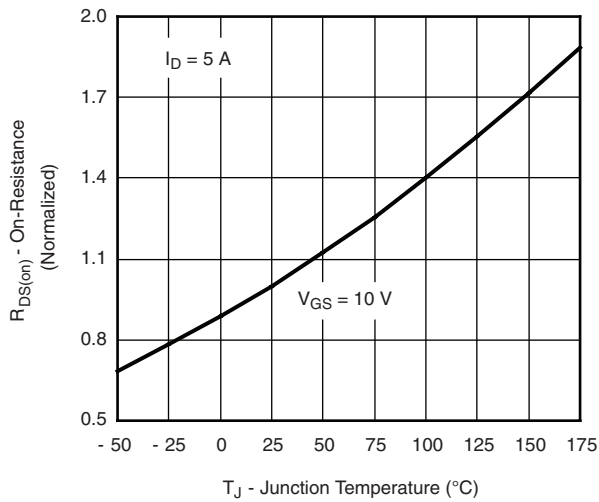


Transconductance

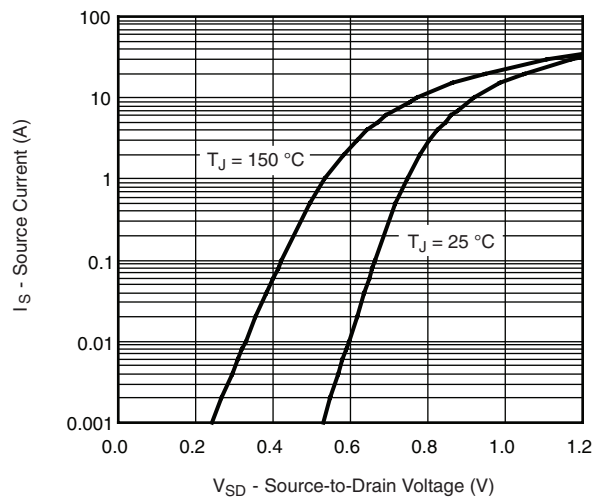


On-Resistance vs. Drain Current

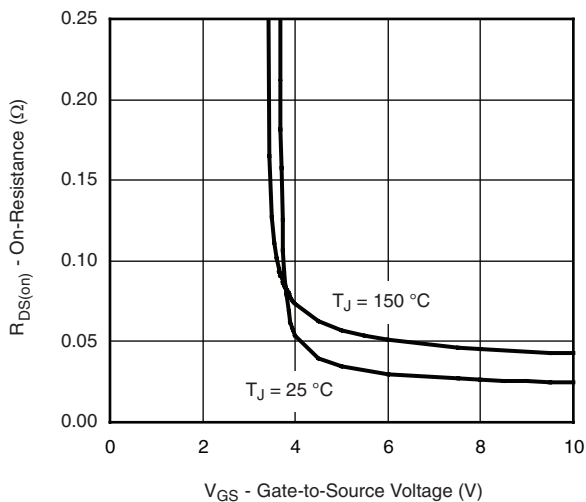
TYPICAL CHARACTERISTICS $T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted



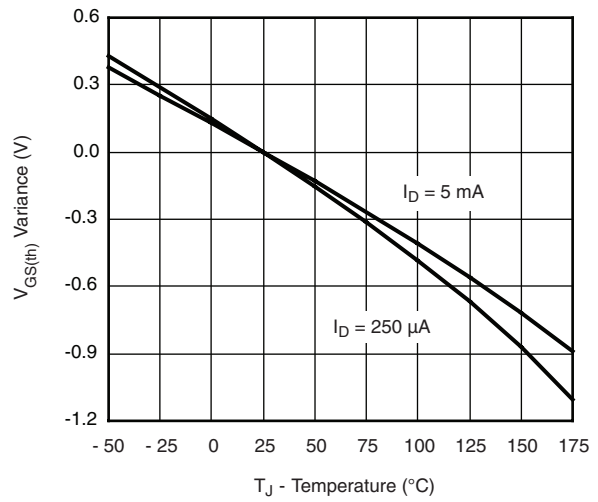
On-Resistance vs. Junction Temperature



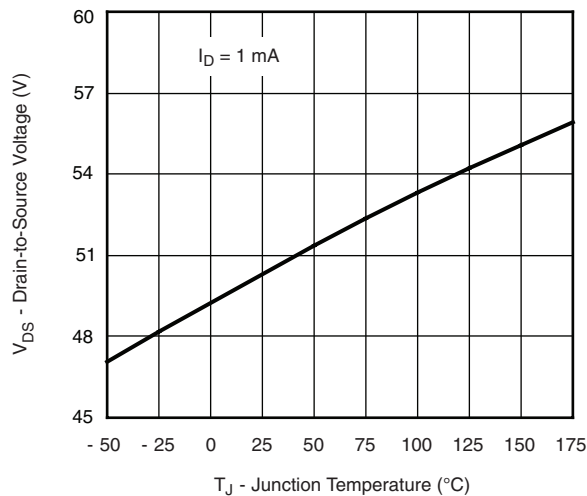
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-Source Voltage

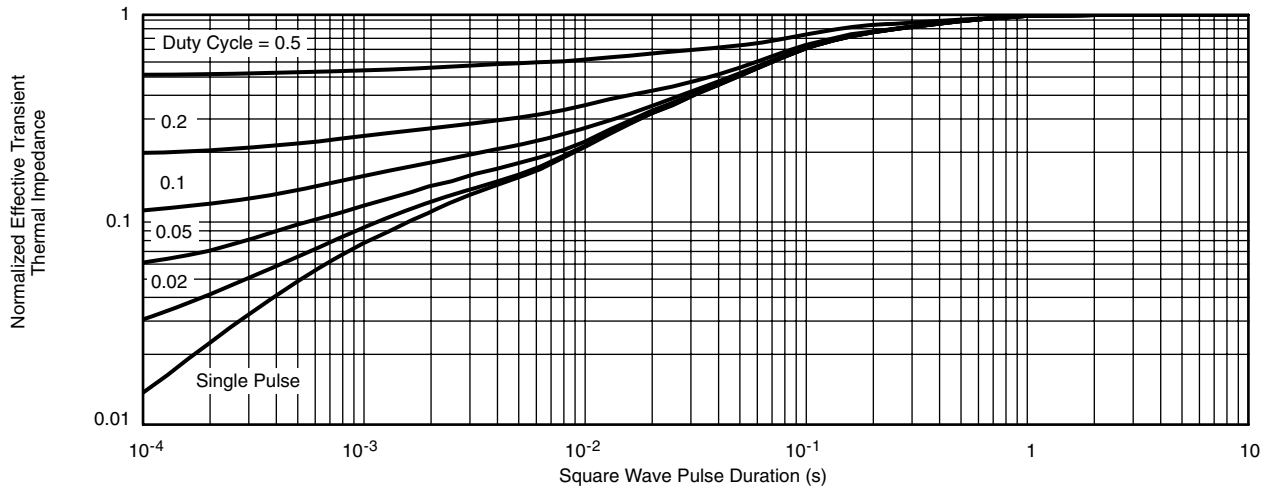


Threshold Voltage



Drain-Source Breakdown vs. Junction Temperature

THERMAL RATINGS $T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted



Normalized thermal Transient Impedance, Junction-to-Foot

Note

The characteristics shown in the graph. Normalized Transient Thermal Impedance Junction to Foot ($25\text{ }^\circ\text{C}$) is given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size $1\text{ }^\prime \times 1\text{ }^\prime \times 0.062\text{ }^\prime$, double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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